

KSC2859

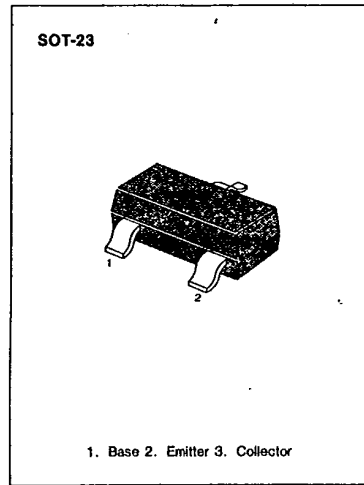
NPN EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER

• Complement to KSA1182

ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	35	V
Collector-Emitter Voltage	V _{CE0}	30	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current	I _C	500	mA
Collector Dissipation	P _C	150	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 ~ 150	°C



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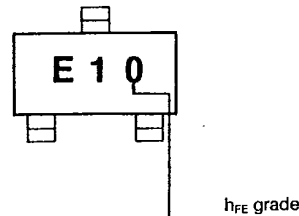
ELECTRICAL CHARACTERISTICS (T_a = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I _{CB0}	V _{CB} =35V, I _E =0			0.1	μA
Emitter Cutoff Current	I _{EB0}	V _{EB} =5V, I _C =0			0.1	μA
DC Current Gain	h _{FE}	V _{CE} =1V, I _C =100mA	70		240	
		V _{CE} =6V, I _C =400mA	25			
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =100mA, I _B =10mA		0.1	0.25	V
Base-Emitter On Voltage	V _{BE(on)}	I _C =100mA, V _{CE} =1V		.08	1.0	V
Current Gain-Bandwidth Product	f _T	I _C =20mA, V _{CE} =6V		300		MHz
Output Capacitance	C _{ob}	V _{CB} =6V, I _E =0 f=1MHz		7		pF

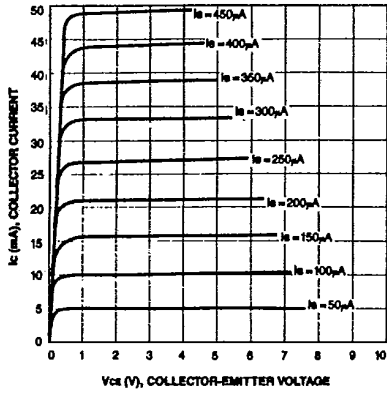
h_{FE} CLASSIFICATION

Classification	O	Y
h _{FE}	70-140	120-240

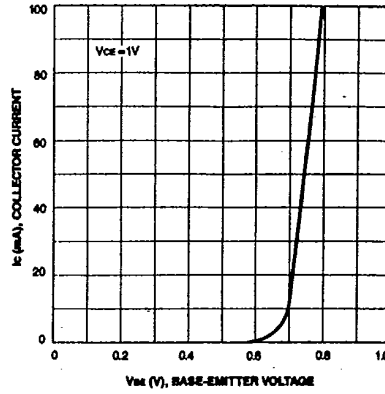
Marking



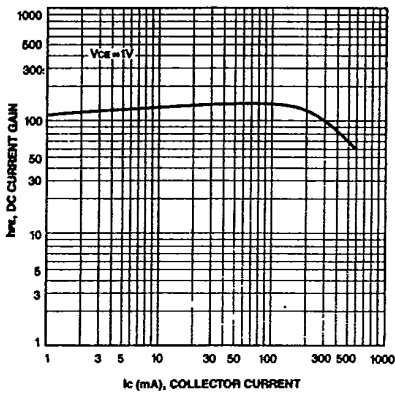
STATIC CHARACTERISTIC



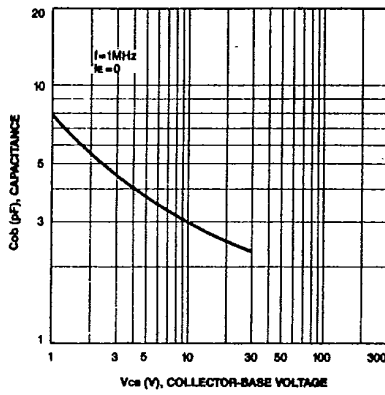
BASE-EMITTER ON VOLTAGE



DC CURRENT GAIN



COLLECTOR OUTPUT CAPACITANCE



BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE

